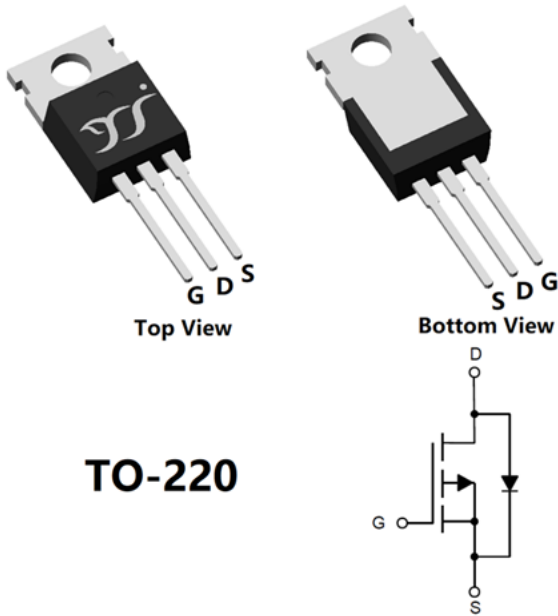


P-Channel Enhancement Mode Field Effect Transistor



TO-220

Product Summary

- V_{DS} -100V
- I_D -23A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) $<85m\Omega$
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) $<100m\Omega$
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Trench Power MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Load switch
- Motor drive control
- DC-DC converter

■ Absolute Maximum Ratings ($T_J=25^\circ C$ unless otherwise noted)

Parameter			Symbol	Limit	Unit	
Drain-source Voltage			V_{DS}	-100	V	
Gate-source Voltage			V_{GS}	± 20	V	
Continuous Drain Current (Note 1,2)	Steady-State	$T_A=25^\circ C, V_{GS}=-10V$	I_D	-4.5	A	
		$T_A=100^\circ C, V_{GS}=-10V$		-2.8		
Continuous Drain Current (Note 1,3)	Steady-State	$T_C=25^\circ C, V_{GS}=-10V$		-23		
		$T_C=100^\circ C, V_{GS}=-10V$		-14.5		
Pulsed Drain Current	$T_C=25^\circ C, t_p=100\mu s$		I_{DM}	-65	A	
Avalanche energy			$V_G=-10V, R_G=25\Omega, L=0.5mH, I_{AS}=-14.3A$	EAS	51.1	mJ
Total Power Dissipation (Note 1,2)	Steady-State	$T_A=25^\circ C$	P_D	3.5	W	
		$T_A=100^\circ C$		1.4		
Total Power Dissipation (Note 1,3)	Steady-State	$T_C=25^\circ C$		125		
		$T_C=100^\circ C$		50		
Junction and Storage Temperature Range			T_J, T_{STG}	-55~+150	$^\circ C$	

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	Steady-State	$R_{\theta JA}$	-	35	$^\circ C/W$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	-	1	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJP085P10A	B1	YJP085P10A	50	/	5000	Tube



YJP085P10A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =-250μA	-100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V	-	-	-1	μA
		V _{DS} =-100V, V _{GS} =0V, T _J =150°C	-	-	-100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =-250μA	-1.5	-2	-2.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-10A	-	65	85	mΩ
		V _{GS} =-4.5V, I _D =-5A	-	72	100	
Diode Forward Voltage	V _{SD}	I _S =-10A, V _{GS} =0V	-	-	-1.2	V
Gate resistance	R _G	f=1MHz	-	10	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	-23	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-50V, V _{GS} =0V, f=1MHz	-	2065	-	pF
Output Capacitance	C _{oss}		-	90	-	
Reverse Transfer Capacitance	C _{rss}		-	72	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =-10V, V _{DS} =-50V, I _D =-10A	-	44.4	-	nC
Gate-Source Charge	Q _{gs}		-	4.7	-	
Gate-Drain Charge	Q _{gd}		-	5.5	-	
Reverse Recovery Charge	Q _{rr}	I _F =-10A, di/dt=100A/us	-	45	-	nC
Reverse Recovery Time	t _{rr}		-	30	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =-10V, V _{DD} =-50V, I _D =-10A R _{GEN} =3Ω	-	9	-	ns
Turn-on Rise Time	t _r		-	42	-	
Turn-off Delay Time	t _{D(off)}		-	91	-	
Turn-off fall Time	t _f		-	31	-	

Note:

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. The value of R_{θJA} is measured with the device mounted on the 40mm*40mm*1.1mm single layer FR-4 PCB board with 1 in² pad of 2oz. Copper, in the still air environment with T_A =25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
3. Thermal resistance from junction to soldering point (on the exposed drain pad).



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Typical Electrical and Thermal Characteristics Diagrams

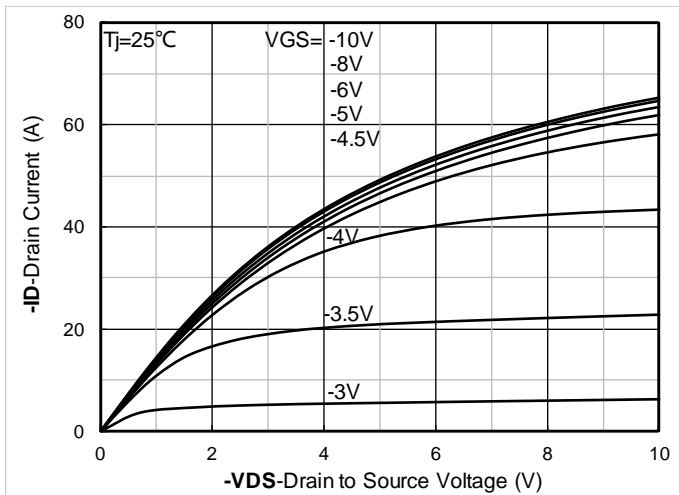


Figure 1. Output Characteristics

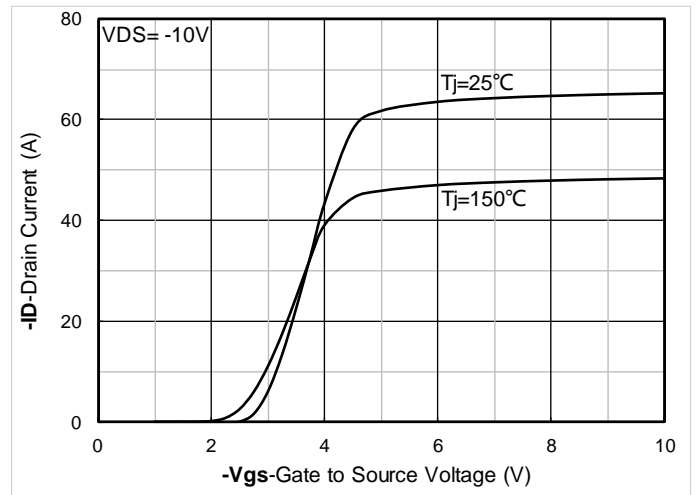


Figure 2. Transfer Characteristics

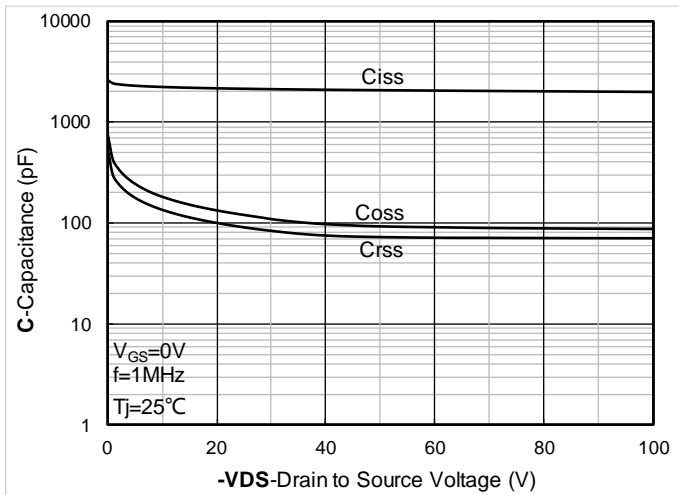


Figure 3. Capacitance Characteristics

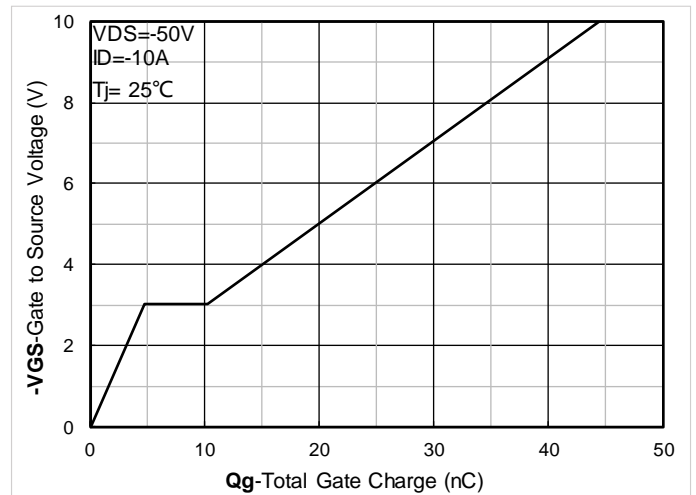


Figure 4. Gate Charge

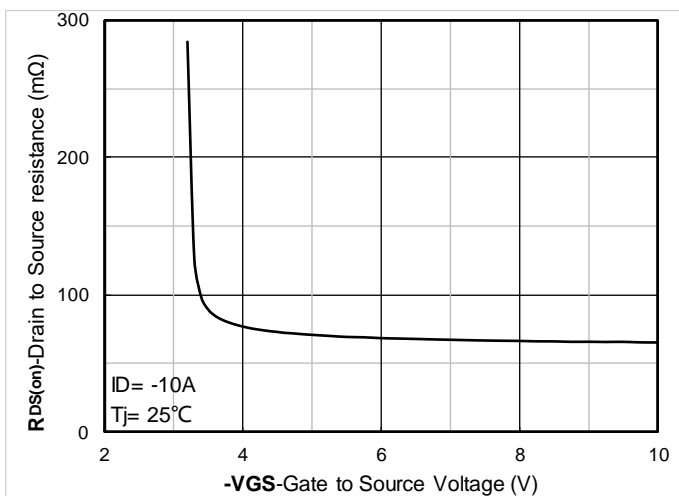


Figure 5. On-Resistance vs Gate to Source Voltage

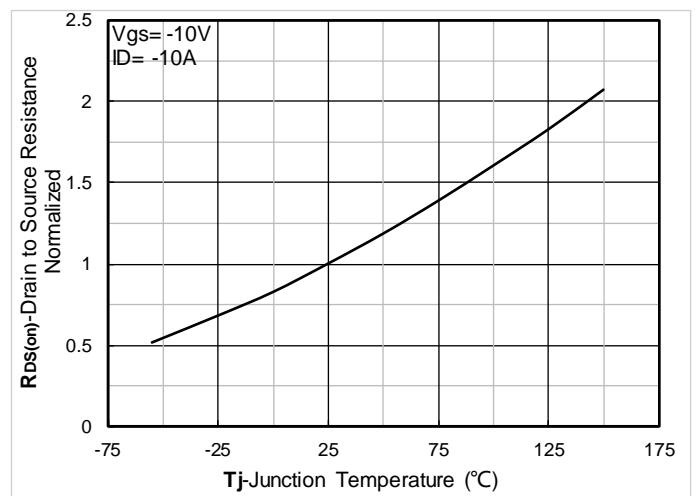


Figure 6. Normalized On-Resistance



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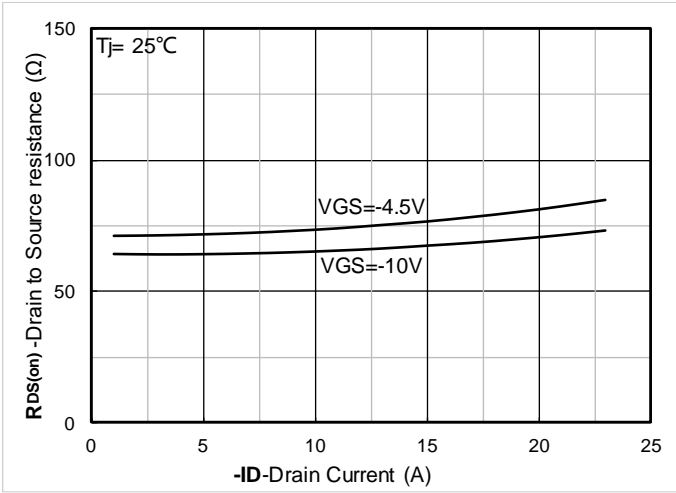


Figure 7. $R_{DS(on)}$ VS Drain Current

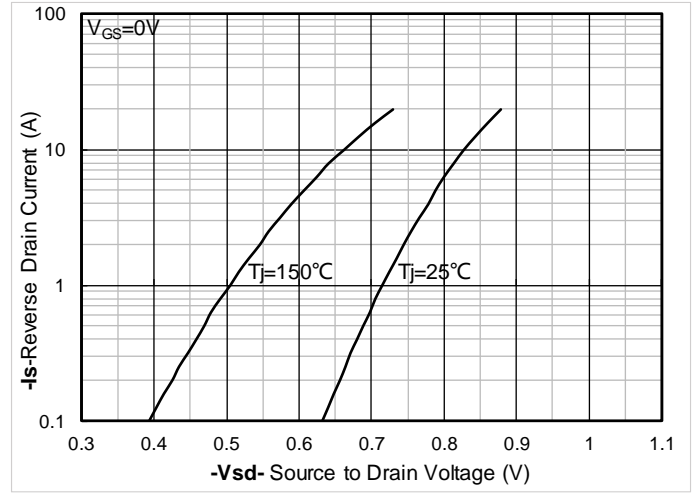


Figure 8. Forward characteristics of reverse diode

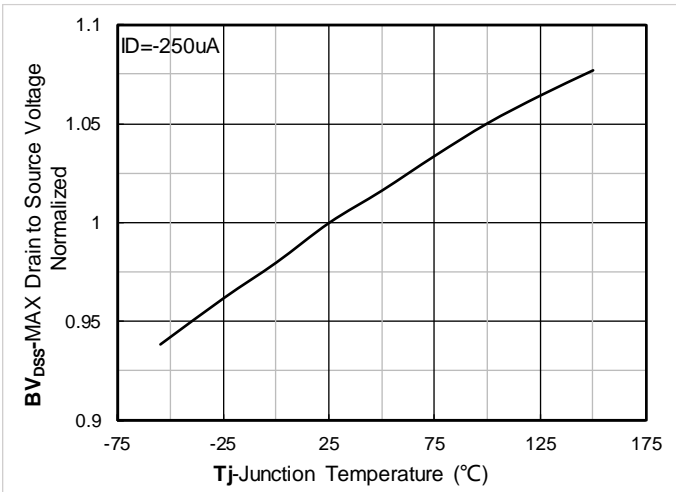


Figure 9. Normalized breakdown voltage

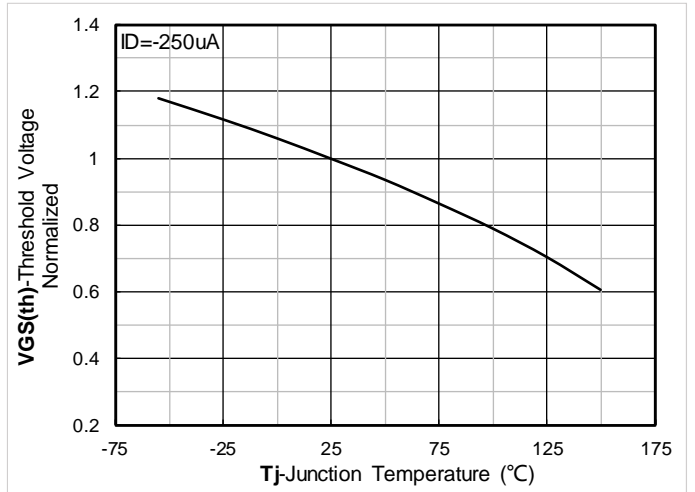


Figure 10. Normalized Threshold voltage

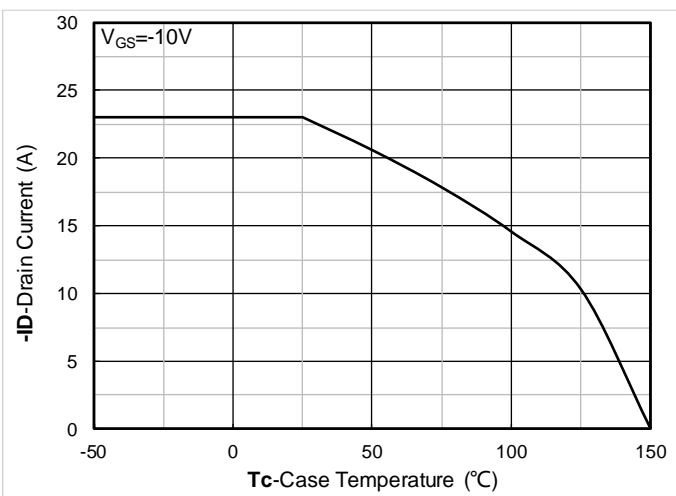


Figure 11. Current dissipation

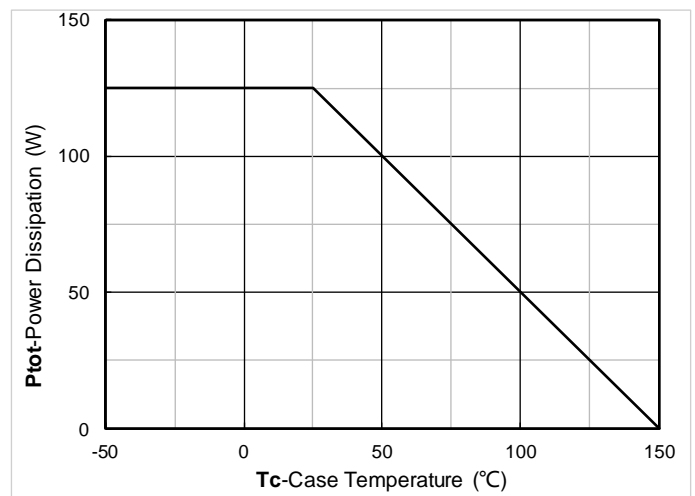


Figure 12. Power dissipation



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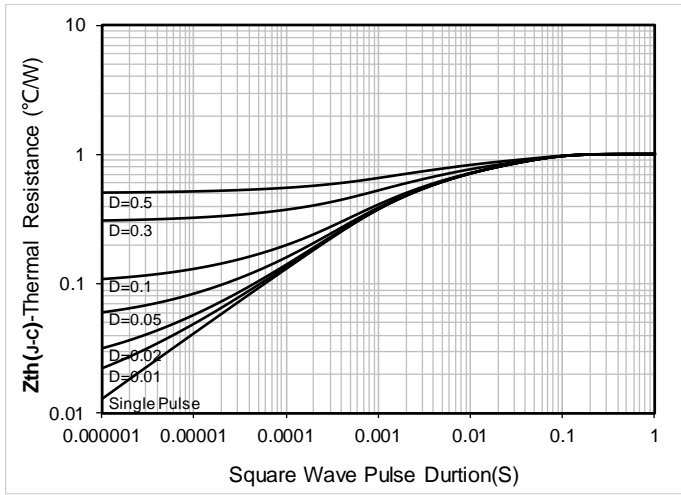


Figure 13. Maximum Transient Thermal Impedance

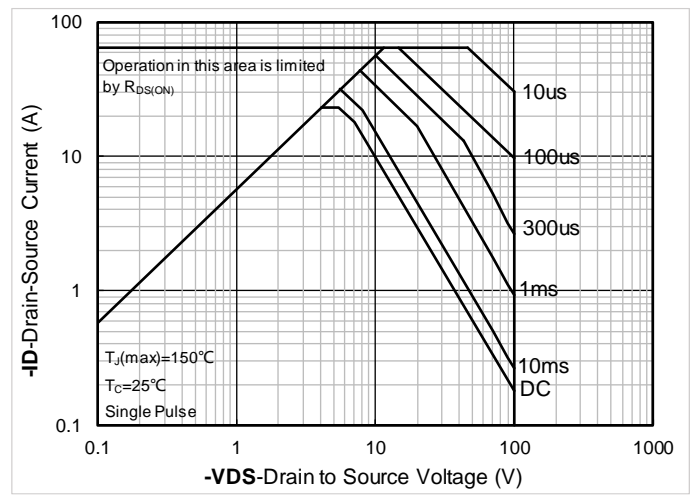
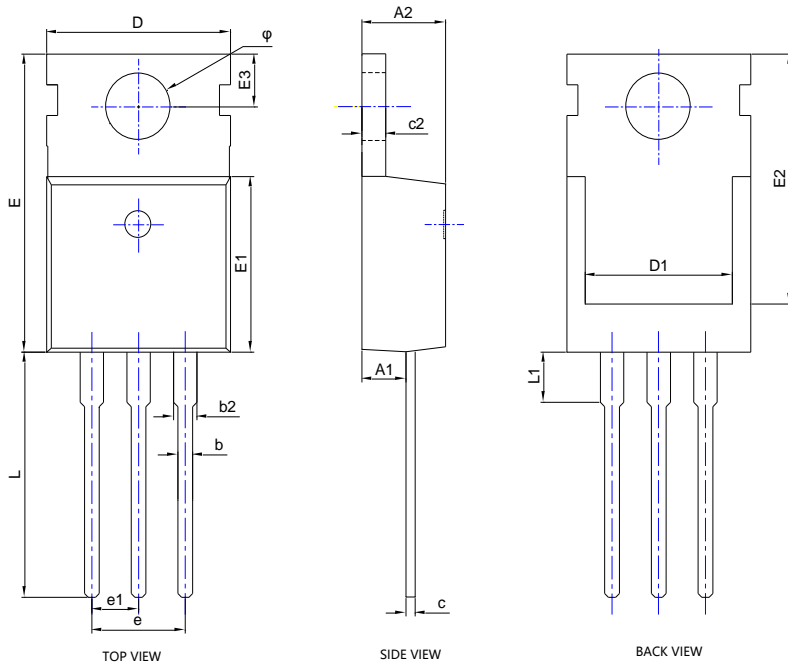


Figure 14. Safe Operation Area



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■ TO-220AB-E Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A1	0.093	0.114	2.350	2.900
A2	0.176	0.184	4.470	4.670
b	0.028	0.036	0.710	0.910
b2	0.048	0.054	1.220	1.360
c	0.019	0.024	0.470	0.600
c2	0.047	0.055	1.200	1.400
D	0.382	0.408	9.700	10.370
D1	0.276	0.350	7.000	8.890
E	0.579	0.622	14.700	15.800
E1	0.350	0.373	8.900	9.470
E2	0.463	0.535	11.750	13.600
E3	0.108BSC		2.740BSC	
e	0.200BSC		5.080BSC	
e1	0.100BSC		2.540BSC	
L	0.508	0.583	12.900	14.800
L1	0.100	0.151	2.540	3.840
φ	0.142	0.154	3.600	3.900

NOTE:
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.



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